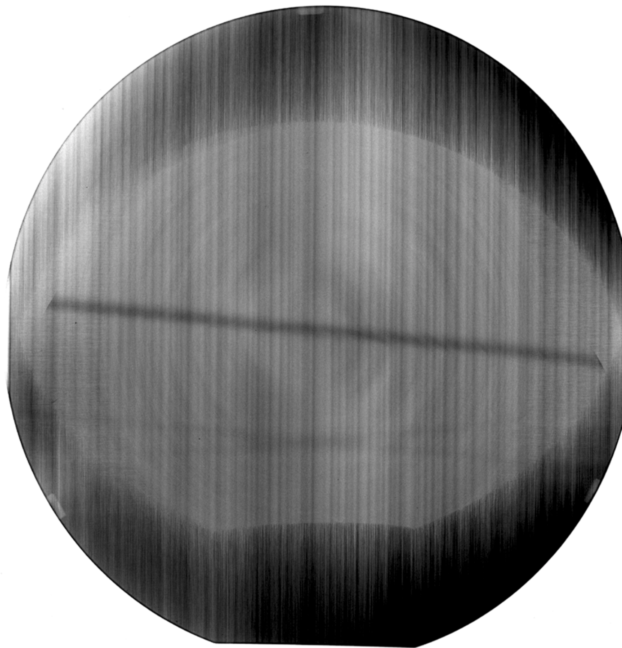
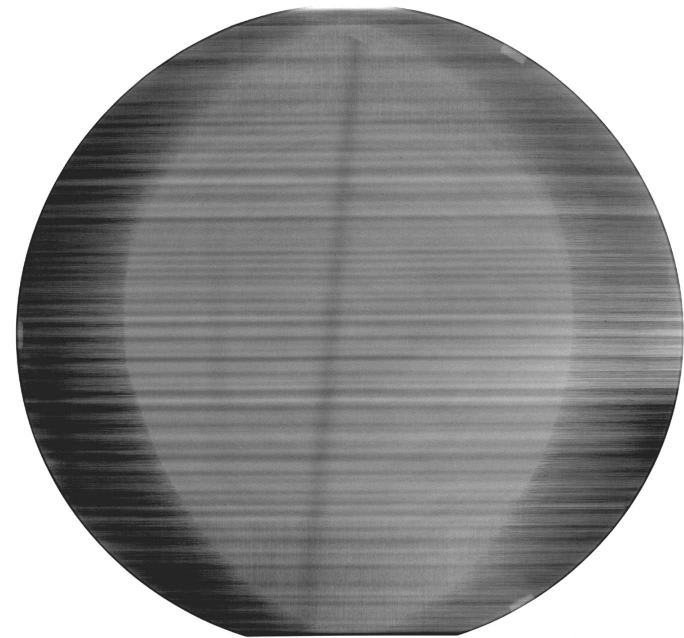
Lang Transmission Topography: 150 mm P/P+ Si Test Wafer

10 μm thick epitaxial layer, special edge treatment, no damage removal





Misfit dislocation distribution around wafer edges.

H. Fukuto, P. Feichtinger, G. D. U'Ren, S. Lindo, M. S. Goorsky, T. Magee, D. Oster, and J. Moreland, J. Crystal Growth **209**, 716-723 (2000